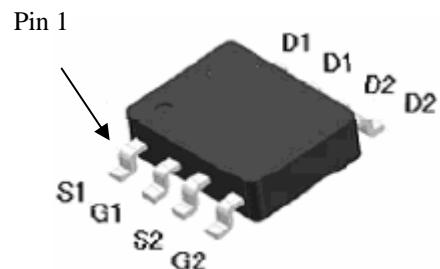


Dual N-Channel Enhancement Mode Power MOSFET

SOP-8

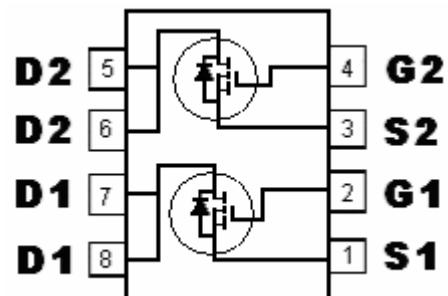
Features:

- Simple drive requirement
- Low on-resistance
- Fast switching speed
- Dual N-ch MOSFET package
- Pb-free lead plating & Halogen-free package



BVDSS	40V
Id	12A
RDS(on)@VGS=10V, Id=8A	20mΩ (typ)
RDS(on)@VGS=4.5V, Id=5A	26mΩ (typ)

KWB25A04Q8



G : Gate S : Source D : Drain

Ordering Information

Device	Package	Shipping
KWB25A04Q8-0-T3-G	SOP-8 (Pb-free lead plating and halogen-free package)	2500 pcs / tape & reel

Absolute Maximum Ratings ($T_a=25^\circ C$)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current @ $V_{GS}=10V$, $T_c=25^\circ C$	I_D	12	A
Continuous Drain Current @ $V_{GS}=10V$, $T_c=100^\circ C$		8.5	
Continuous Drain Current @ $V_{GS}=10V$, $T_A=25^\circ C$		8 (Note 2)	
Continuous Drain Current @ $V_{GS}=10V$, $T_A=70^\circ C$		6.7 (Note 2)	
Pulsed Drain Current	I_{DM}	32 (Note 1)	
Power Dissipation for Dual Operation	P_D	3	W
Power Dissipation for Single Operation		2.4 (Note 2)	
Operating Junction and Storage Temperature Range	T_j , T_{stg}	-55~+150	

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	25	°C/W
Thermal Resistance, Junction-to-ambient, max	$R_{th,j-a}$	62.5 (Note 2) 125 (Note 3)	

Note : 1. Pulse width limited by maximum junction temperature
 2. Surface mounted on 1 in² copper pad of FR-4 board, pulse width≤10s.
 3. Surface mounted on minimum copper pad, pulse width≤10s.

Characteristics ($T_j=25^\circ C$, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	40	-	-	V	$V_{GS}=0$, $I_D=250\mu A$
$V_{GS(th)}$	1.0	1.4	2.5	V	$V_{DS}=V_{GS}$, $I_D=250\mu A$
G_{FS} *1	-	10	-	S	$V_{DS}=5V$, $I_D=8A$
I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 20$, $V_{DS}=0$
I_{DSS}	-	-	1	μA	$V_{DS}=32V$, $V_{GS}=0$
	-	-	25	μA	$V_{DS}=32V$, $V_{GS}=0$, $T_j=125^\circ C$
$R_{DS(ON)}$ *1	-	20	25	$m\Omega$	$V_{GS}=10V$, $I_D=8A$
	-	26	35	$m\Omega$	$V_{GS}=4.5V$, $I_D=5A$
Dynamic					
Q_g *1, 2	-	9	-	nC	$V_{DS}=20V$, $I_D=8A$, $V_{GS}=10V$
Q_{gs} *1, 2	-	1.8	-		
Q_{gd} *1, 2	-	2.5	-		
$t_{d(ON)}$ *1, 2	-	7	-	ns	$V_{DS}=20V$, $I_D=1A$, $V_{GS}=10V$, $R_G=6\Omega$
t_r *1, 2	-	5	-		
$t_{d(OFF)}$ *1, 2	-	21	-		
t_f *1, 2	-	8	-		



C _{iss}	-	640	-	pF	V _{GS} =0V, V _{DS} =20V, f=1MHz
C _{oss}	-	51	-		
C _{rss}	-	45	-		
Source-Drain Diode					
I _S *1	-	-	8	A	V _{SD} =1A, V _{GS} =0V
I _{SM} *3	-	-	24		
V _{SD} *1	-	0.73	1.2		

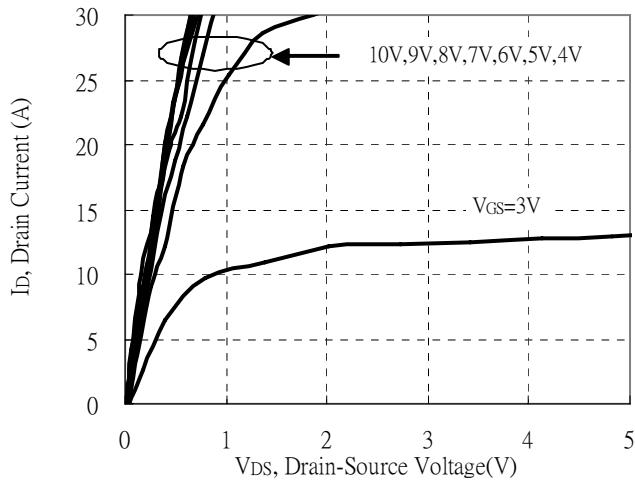
Note : *1.Pulse Test : Pulse Width \leq 300μs, Duty Cycle \leq 2%

*2.Independent of operating temperature

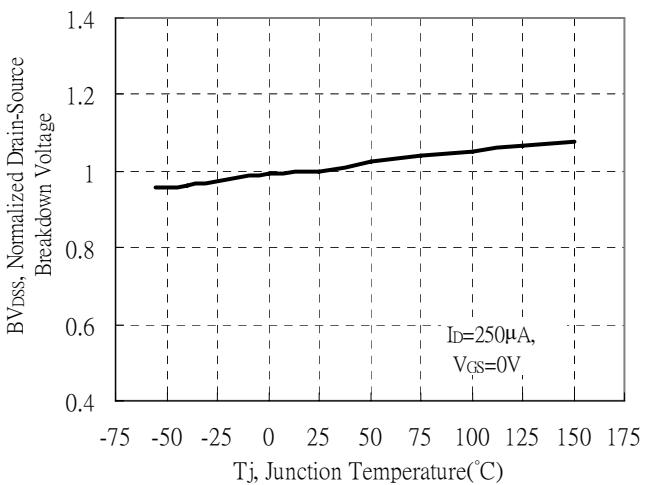
*3.Pulse width limited by maximum junction temperature.

Typical Characteristics

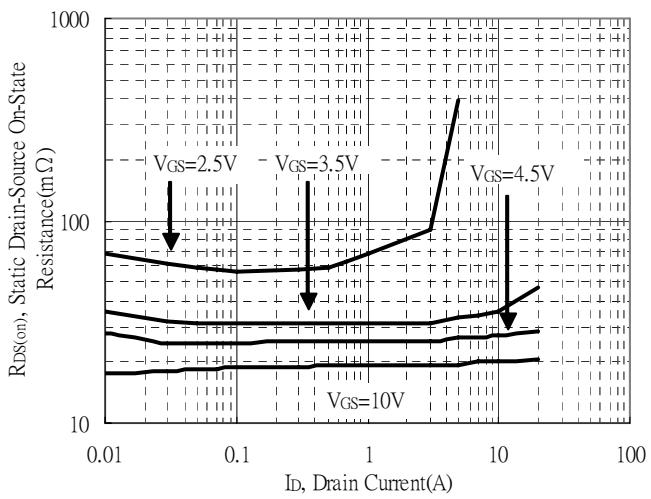
Typical Output Characteristics



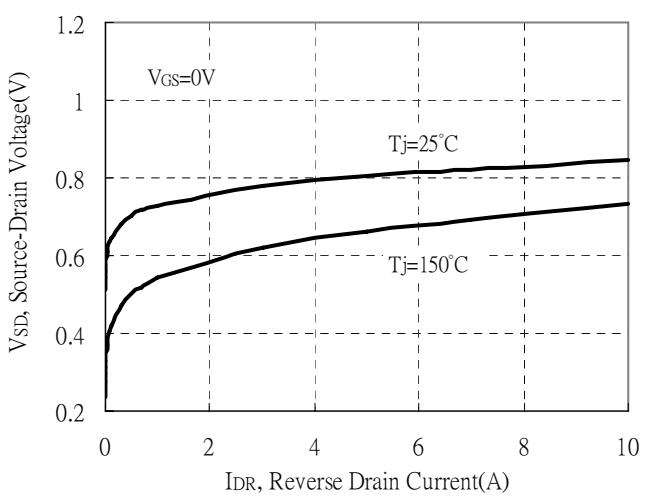
Breakdown Voltage vs Ambient Temperature



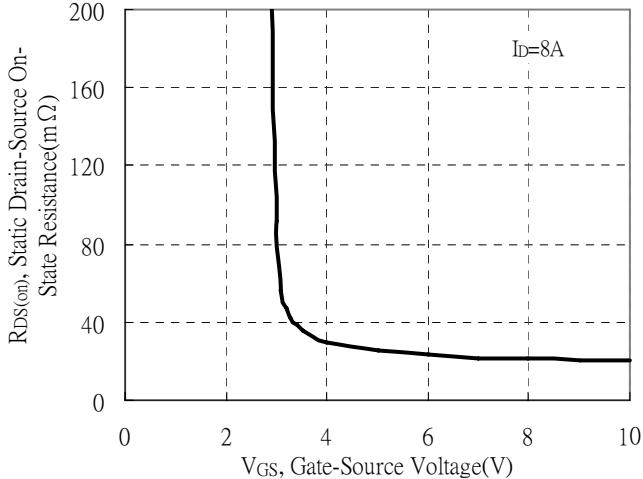
Static Drain-Source On-State resistance vs Drain Current



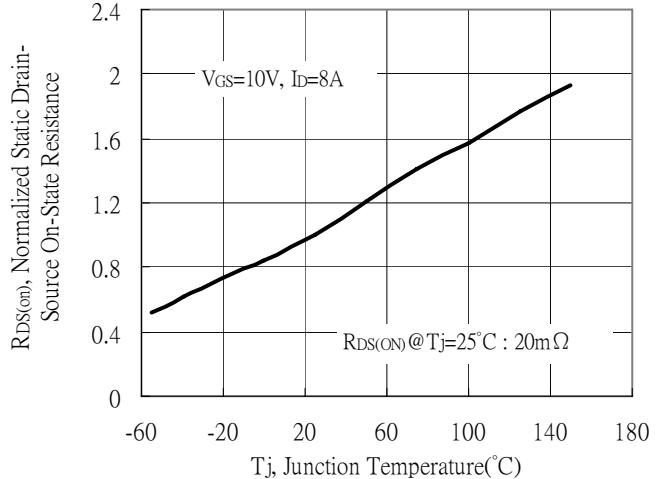
Reverse Drain Current vs Source-Drain Voltage



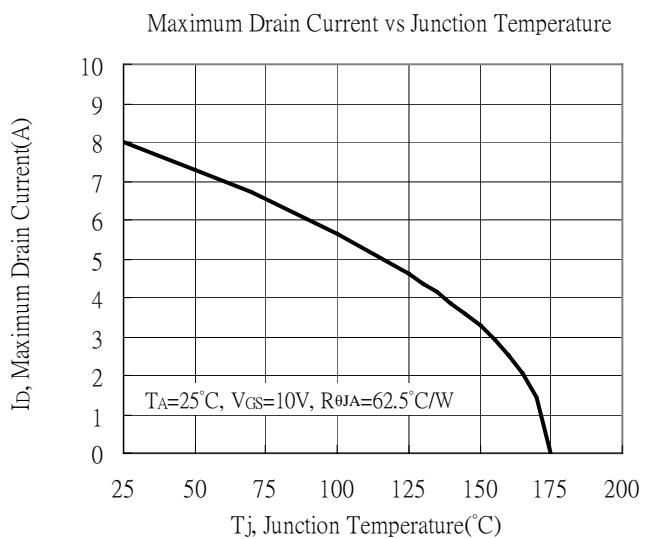
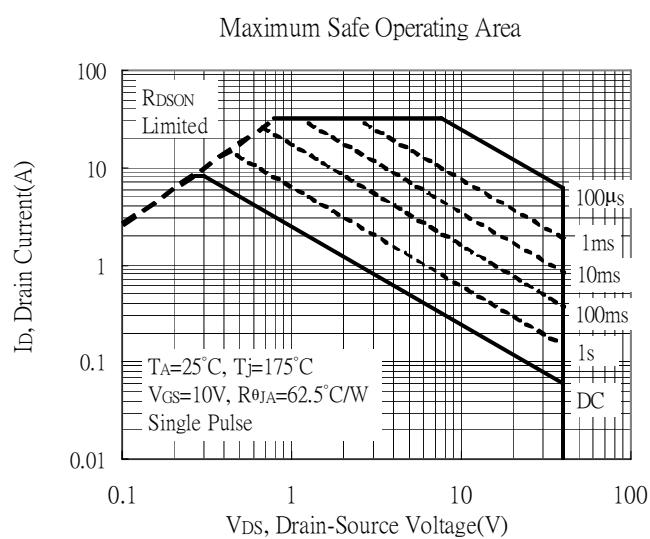
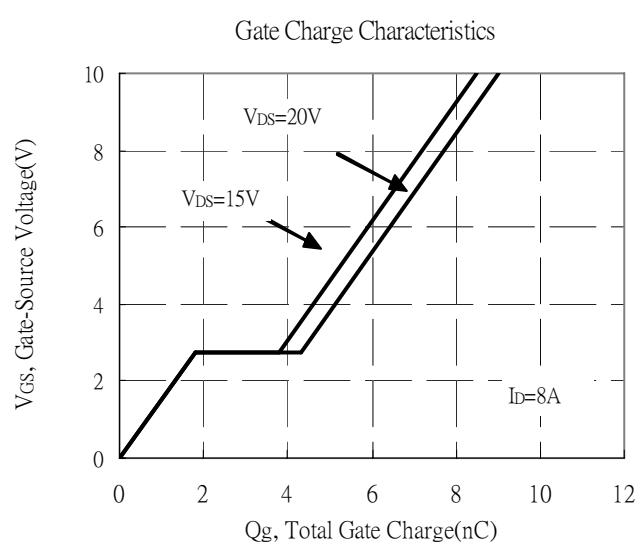
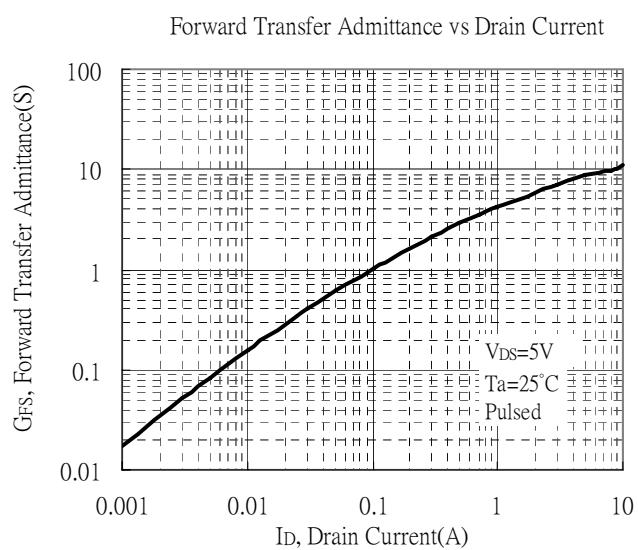
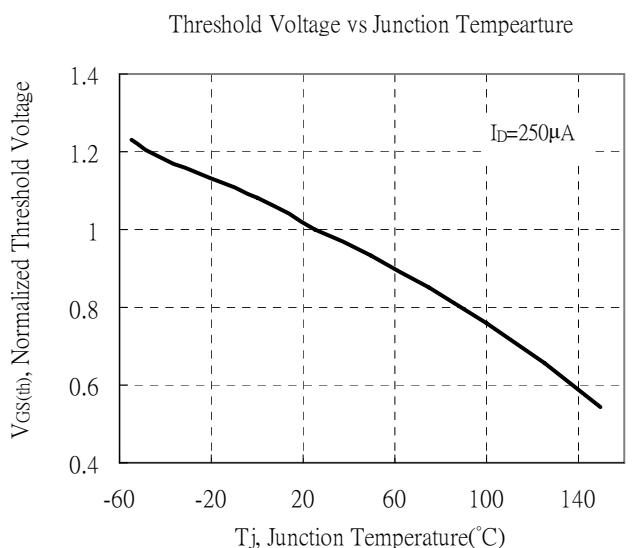
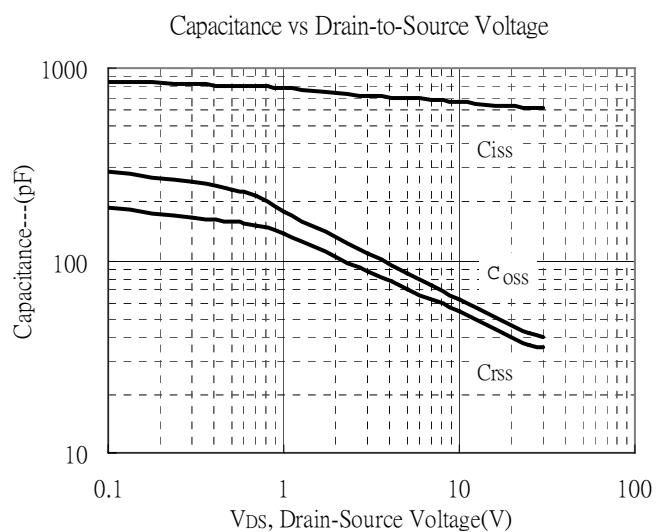
Static Drain-Source On-State Resistance vs Gate-Source Voltage



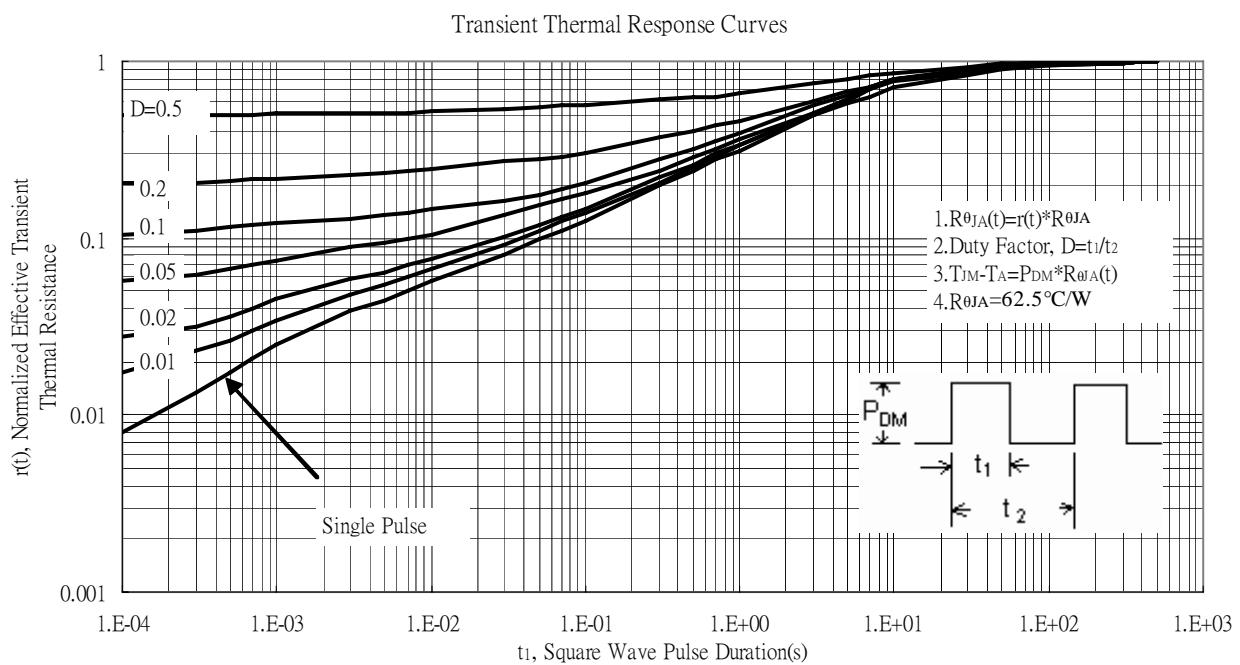
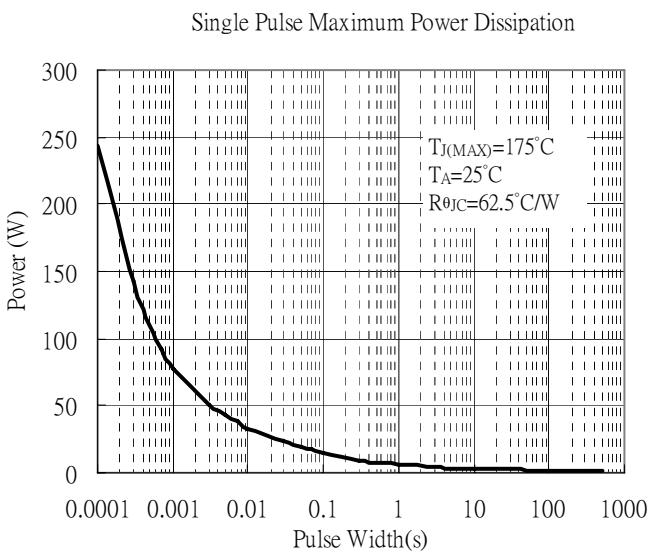
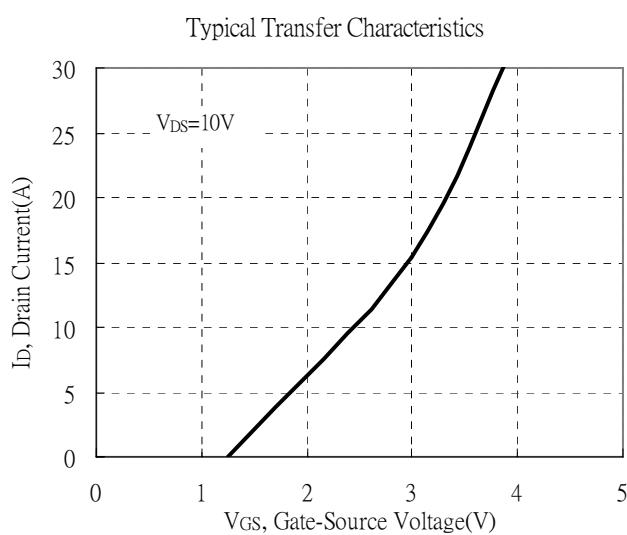
Drain-Source On-State Resistance vs Junction Temperature



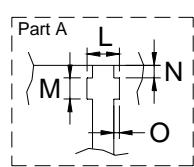
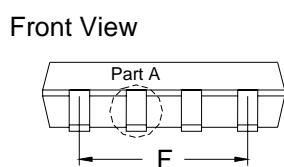
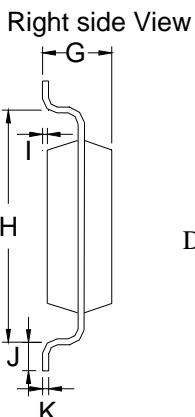
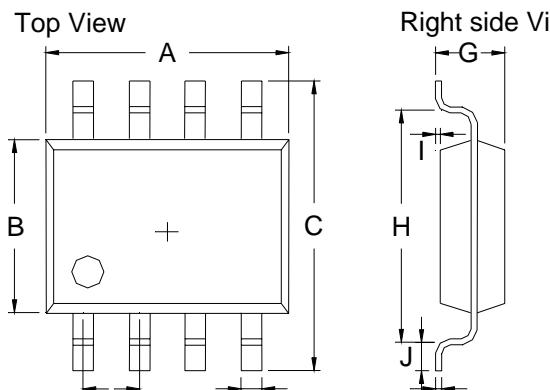
Typical Characteristics(Cont.)



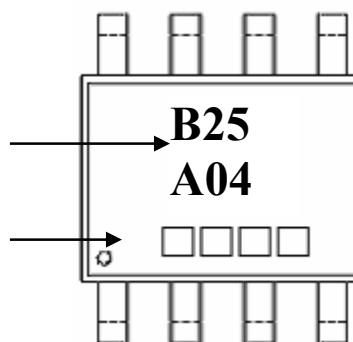
Typical Characteristics(Cont.)



SOP-8 Dimension



Marking:



8-Lead SOP-8 Plastic Package
Code: Q8

*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1850	0.2007	4.70	5.10	I	0.0031	0.0110	0.08	0.28
B	0.1457	0.1614	3.70	4.10	J	0.0157	0.0323	0.40	0.83
C	0.2283	0.2441	5.80	6.20	K	0.0074	0.0102	0.19	0.26
D	0.0500*		1.27*		L	0.0145	0.0204	0.37	0.52
E	0.0130	0.0201	0.33	0.51	M	0.0118	0.0197	0.30	0.50
F	0.1472	0.1527	3.74	3.88	N	0.0031	0.0051	0.08	0.13
G	0.0472	0.0638	1.20	1.62	O	0.0000	0.0059	0.00	0.15
H	0.1889	0.2007	4.80	5.10					